

General Description

The 060N10 uses advanced technology and design to provide excellent RDS(ON). This device is ideal for PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current	60	A
I_{DM}	Pulsed Drain Current	320	A
EAS	Single Pulse Avalanche Energy ¹	612	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation	100	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (PCB mount)	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	1.5	$^\circ C/W$

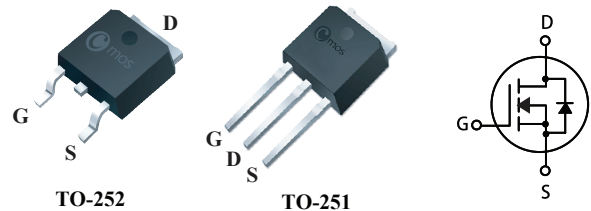
Product Summary

BVDSS	RDSON	ID
100V	7m Ω	80A

Applications

- DC-DC Converters
- Power switching application

TO-252/251 Pin Configuration



Type	Package	Marking
CMD060N10	TO-252	CMD060N10
CMU060N10	TO-251	CMU060N10

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=28A$	---	---	7	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=20A$	---	20	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=50V, I_D=27.5A$ $V_{GS}=10V$	---	45	---	nC
Q_{gs}	Gate-Source Charge		---	12	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, I_D=27.5A$ $R_G=4.7\Omega, R_L=1.82\Omega$	---	23	---	ns
T_r	Rise Time		---	9	---	
$T_{d(off)}$	Turn-Off Delay Time		---	63	---	
T_f	Fall Time		---	19	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	3500	---	pF
C_{oss}	Output Capacitance		---	1250	---	
C_{rss}	Reverse Transfer Capacitance		---	60	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	80	A
I_{SM}	Pulsed Source Current		---	---	320	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=28A, T_J=25^\circ\text{C}$	---	---	1.2	V

Notes:

1.The EAS data shows Max. rating . The test condition is $V_{DD}=40V, V_{GS}=10V, L=0.5\text{mH}, I_D=49.5A$

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